
Li-Ion BATTERY PROTECTOR

RN5VM1××C/D SERIES

APPLICATION MANUAL

RICOH

ELECTRONIC DEVICES DIVISION

NO. EA-041-9803

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June 1995

RN5VM1××C/D Series

APPLICATION MANUAL

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RN5VM1××C/D SERIES

OUTLINE

The RN5VM Series are protection ICs for over-charge/discharge of rechargeable one-cell Lithium-ion (Li+) batteries by CMOS process.

The RN5VM Series can detect over-charge/discharge of Li+ one-cell and excess load current, further include a short circuit protector for preventing large external short circuit current.

Each of these ICs is composed of three voltage detectors, a reference unit, a hysteresis circuit, and a short circuit protector. When charging voltage crosses the detector threshold from a low value to a value higher than V_{DET1} , the output of COUT pin, the output of over-charge detector/VD1, switches to low level, ..charger's negative pin level. After detecting over-charge the VD1 can be reset and the output of COUT pin becomes "H" when the VDD voltage is coming down to a level lower than " $V_{DET1} - V_{HYS1}$ ", or when a charger is disconnected from the battery pack while the VDD level is in between " V_{DET1} " and " $V_{DET1} - V_{HYS1}$ " in the RN5VM1××C version.

While in the RN5VM1××D version after detecting over-charge, any load current can not be drawn from the battery pack when the VDD voltage stays over " $V_{DET1} - V_{HYS1}$ ", excepting that the VD1 can be reset and it allows to draw load current when the VDD voltage is coming down to a level lower than " $V_{DET1} - V_{HYS1}$ " because of a cell internal discharging.

The output of DOUT pin, the output of over-discharge detector/VD2, switches to "L" after internally fixed delay time passed, when discharging voltage crosses the detector threshold from a high value to a value lower than V_{DET2} . An excess load current can be sensed and cut off after internally fixed delay time passed through the built in excess current detector, VD3, with DOUT being enabled to low level. Once after detecting excess current, the VD3 is released and DOUT level switches to "H" by detaching a battery pack from a load system.

Further, short circuit protector makes DOUT level to "L" immediately with external short circuit current and removing external short circuit leads DOUT level to "H". After detecting over-discharge, supply current will be kept extremely "L" by halting some internal circuits operation. The output delay of over-charge detectors can be set by connecting external capacitors. Output type of COUT and DOUT are CMOS. SOT23-6 is available.

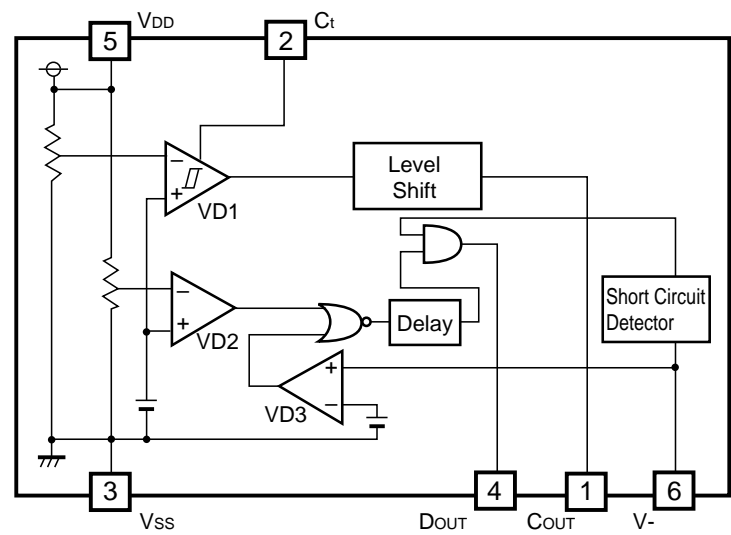
FEATURES

- Low supply currentSupply current TYP. 3.0μA
Standby current (after detecting over-discharge) TYP. 0.3μA
- High withstand voltage.....Absolute maximum ratings 28V ($V_{DD}-V$)
- High accuracy detector thresholdOver-charge detector ±50mV
Over-discharge detector ±2.5%
- Variety of detector threshold.....Over-charge detector threshold 4.0V to 4.4V/step of 0.01V
Over-discharge detector threshold 2.0V to 3.0V/step of 0.05V
- Built-in protection circuit.....Excess current trip/Short circuit protector
- Output delay of over-chargeTime delay at $C_3=0.01\mu F$ and $V_{DD}=4.3V$ 75ms for RN5VM111×
- Ultra small packageSOT-23-6

APPLICATIONS

- Over-charge/over-discharge protection for Li+ one-cell pack
- High precision protectors for cell-phones and any other gadgets using on board Li+ one-cell battery

BLOCK DIAGRAM



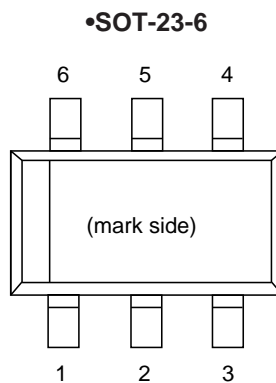
SELECTION GUIDE

In the RN5VM1××× Series three of the input threshold for over-charge, over-discharge and excess current and taping type can be designating at the user's request by Part Number as follows:

RN5VM1×××-×× ←Part Number
 ↑ ↑ ↑
 a b c

Code	Description
a	Serial Number for the RN5VM Series designating input threshold for over-charge, over-discharge and excess current detectors as well as hysteresis range for over-charge detector.
b	Designation of version symbols C : drawing load current is allowable after detecting over-charge. D : drawing load current is not allowable after detecting over-charge.
c	Designation of Taping Type: TR (refer to Taping Specification)

PIN CONFIGURATION



PIN DESCRIPTION

Pin No.	Symbol	Pin description
1	COUT	Output of over-charge detection, CMOS output
2	Ct	Pin for external capacitor setting output delay of VD1
3	VSS	Ground
4	DOUT	Output of over-discharge detection, CMOS output
5	VDD	Power supply
6	V-	Pin for charger negative input

ABSOLUTE MAXIMUM RATINGS

V_{SS}=0V

Symbol	Item		Rating	Unit
V _{DD}	Supply Voltage		−0.3 to 12	V
V ₋	Input Voltage	V ₋ pin	V _{DD} −28 to V _{DD} +0.3	V
V _{ct}		Ct pin	V _{SS} −0.3 to V _{DD} +0.3	V
V _{COUT}	Output Voltage	COUT pin	V _{DD} −28 to V _{DD} +0.3	V
V _{DOUT}		DOUT pin	V _{SS} −0.3 to V _{DD} +0.3	V
P _D	Power Dissipation		150	mW
T _{opt}	Operating Temperature Range		−40 to +85	°C
T _{stg}	Storage Temperature Range		−55 to +125	°C

ABSOLUTE MAXIMUM RATINGS

Absolute Maximum ratings are threshold limit values that must not be exceeded even for an instant under any conditions. Moreover, such values for any two items must not be reached simultaneously. Operation above these absolute maximum ratings may cause degradation or permanent damage to the device. These are stress ratings only and do not necessarily imply functional operation below these limits.

ELECTRICAL CHARACTERISTIC

• RN5VM111C

T_{opt}=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD1}	Operating input voltage	Voltage defined as V _{DD} –V _{SS}	1.5		10	V
V _{st}	Minimum operating voltage for 0V charging	Voltage defined as V _{DD} –V ₋ , V _{DD} –V _{SS} =0V			1.2	V
V _{DET1}	Over-charge threshold voltage	Detect rising edge of supply voltage	4.20	4.25	4.30	V
V _{HYS1}	Over-charge threshold hysteresis range		0.15	0.2	0.25	V
t _{DET1}	Output delay time of over-charge	C ₃ =0.01μF, V _{DD} =3.6V→4.3V	50	75	100	ms
V _{DET2}	Over-discharge threshold voltage	Detect falling edge of supply voltage	2.437	2.50	2.563	V
t _{DET2}	Output delay time of over-discharge	V _{DD} =3.6V→2.4V	7	10	13	ms
V _{DET3}	Excess current threshold voltage	Detect rising edge of “V-” pin voltage	0.17	0.20	0.23	V
t _{DET3}	Output delay time of excess current	V _{DD} =3.0V	9	13	17	ms
V _{short}	Short detection voltage	V _{DD} =3.0V	V _{DD} –1.1	V _{DD} –0.8	V _{DD} –0.5	V
t _{short}	Output delay time of short detection	V _{DD} =3.0V		5	50	μs
R _{short}	Reset resistance for excess current protection	V _{DD} =3.6V, V ₋ =1.0V	50	100	150	kΩ
V _{OL1}	Nch ON voltage of C _{OUT}	I _{OL} =50μA, V _{DD} =4.4V		0.2	0.5	V
V _{OH1}	Pch ON voltage of C _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.8		V
V _{OL2}	Nch ON voltage of D _{OUT}	I _{OL} =50μA, V _{DD} =2.4V		0.2	0.5	V
V _{OH2}	Pch ON voltage of D _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.7		V
I _{DD}	Supply current	V _{DD} =3.9V, V ₋ =0V		3.0	6.0	μA
I _{standby}	Standby current	V _{DD} =2.0V		0.3	0.6	μA

■ ★) Please refer to Test Circuit unless otherwise specified.

• RN5VM112C

T_{opt}=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD1}	Operating input voltage	Voltage defined as V _{DD} –V _{SS}	1.5		10	V
V _{st}	Minimum operating voltage for 0V charging	Voltage defined as V _{DD} –V _– , V _{DD} –V _{SS} =0V			1.2	V
V _{DET1}	Over-charge threshold voltage	Detect rising edge of supply voltage	4.30	4.35	4.40	V
V _{HYS1}	Over-charge threshold hysteresis range		0.15	0.20	0.25	V
t _{VDET1}	Output delay time of over-charge	C ₃ =0.01μF, V _{DD} =3.6V→4.4V	55	80	105	ms
V _{DET2}	Over-discharge threshold voltage	Detect falling edge of supply voltage	2.437	2.500	2.563	V
t _{VDET2}	Output delay time of over-discharge	V _{DD} =3.6V→2.4V	7	10	13	ms
V _{DET3}	Excess current threshold voltage	Detect rising edge of “V-” pin voltage	0.17	0.20	0.23	V
t _{VDET3}	Output delay time of excess current	V _{DD} =3.0V	9	13	17	ms
V _{short}	Short detection voltage	V _{DD} =3.0V	V _{DD} –1.1	V _{DD} –0.8	V _{DD} –0.5	V
t _{short}	Output delay time of short detection	V _{DD} =3.0V		5	50	μs
R _{short}	Reset resistance for excess current protection	V _{DD} =3.6V, V _– =1.0V	50	100	150	kΩ
V _{OL1}	Nch ON voltage of C _{OUT}	I _{OL} =50μA, V _{DD} =4.4V		0.2	0.5	V
V _{OH1}	Pch ON voltage of C _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.8		V
V _{OL2}	Nch ON voltage of D _{OUT}	I _{OL} =50μA, V _{DD} =2.4V		0.2	0.5	V
V _{OH2}	Pch ON voltage of D _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.7		V
I _{DD}	Supply current	V _{DD} =3.9V, V _– =0V		3.0	6.0	μA
I _{standby}	Standby current	V _{DD} =2.0V		0.3	0.6	μA

■ *) Please refer to Test Circuit unless otherwise specified.

• RN5VM111D

T_{opt}=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD1}	Operating input voltage	Voltage defined as V _{DD} –V _{SS}	1.5		10	V
V _{st}	Minimum operating voltage for 0V charging	Voltage defined as V _{DD} –V _– , V _{DD} –V _{SS} =0V			1.2	V
V _{DET1}	Over-charge threshold voltage	Detect rising edge of supply voltage	4.20	4.25	4.30	V
V _{HYS1}	Over-charge threshold hysteresis range		0.15	0.20	0.25	V
t _{VDET1}	Output delay time of over-charge	C ₃ =0.01μF, V _{DD} =3.6V→4.3V	50	75	100	ms
V _{DET2}	Over-discharge threshold voltage	Detect falling edge of supply voltage	2.437	2.500	2.563	V
t _{VDET2}	Output delay time of over-discharge	V _{DD} =3.6V→2.4V	7	10	13	ms
V _{DET3}	Excess current threshold voltage	Detect rising edge of “V-” pin voltage	0.17	0.20	0.23	V
t _{VDET3}	Output delay time of excess current	V _{DD} =3.0V	9	13	17	ms
V _{short}	Short detection voltage	V _{DD} =3.0V	V _{DD} –1.1	V _{DD} –0.8	V _{DD} –0.5	V
t _{short}	Output delay time of short detection	V _{DD} =3.0V		5	50	μs
R _{short}	Reset resistance for excess current protection	V _{DD} =3.6V, V _– =1.0V	50	100	150	kΩ
V _{OL1}	Nch ON voltage of C _{OUT}	I _{OL} =50μA, V _{DD} =4.4V		0.2	0.5	V
V _{OH1}	Pch ON voltage of C _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.8		V
V _{OL2}	Nch ON voltage of D _{OUT}	I _{OL} =50μA, V _{DD} =2.4V		0.2	0.5	V
V _{OH2}	Pch ON voltage of D _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.7		V
I _{DD}	Supply current	V _{DD} =3.9V, V _– =0V		3.0	6.0	μA
I _{standby}	Standby current	V _{DD} =2.0V		0.3	0.6	μA

■ *) Please refer to Test Circuit unless otherwise specified.

• RN5VM112D

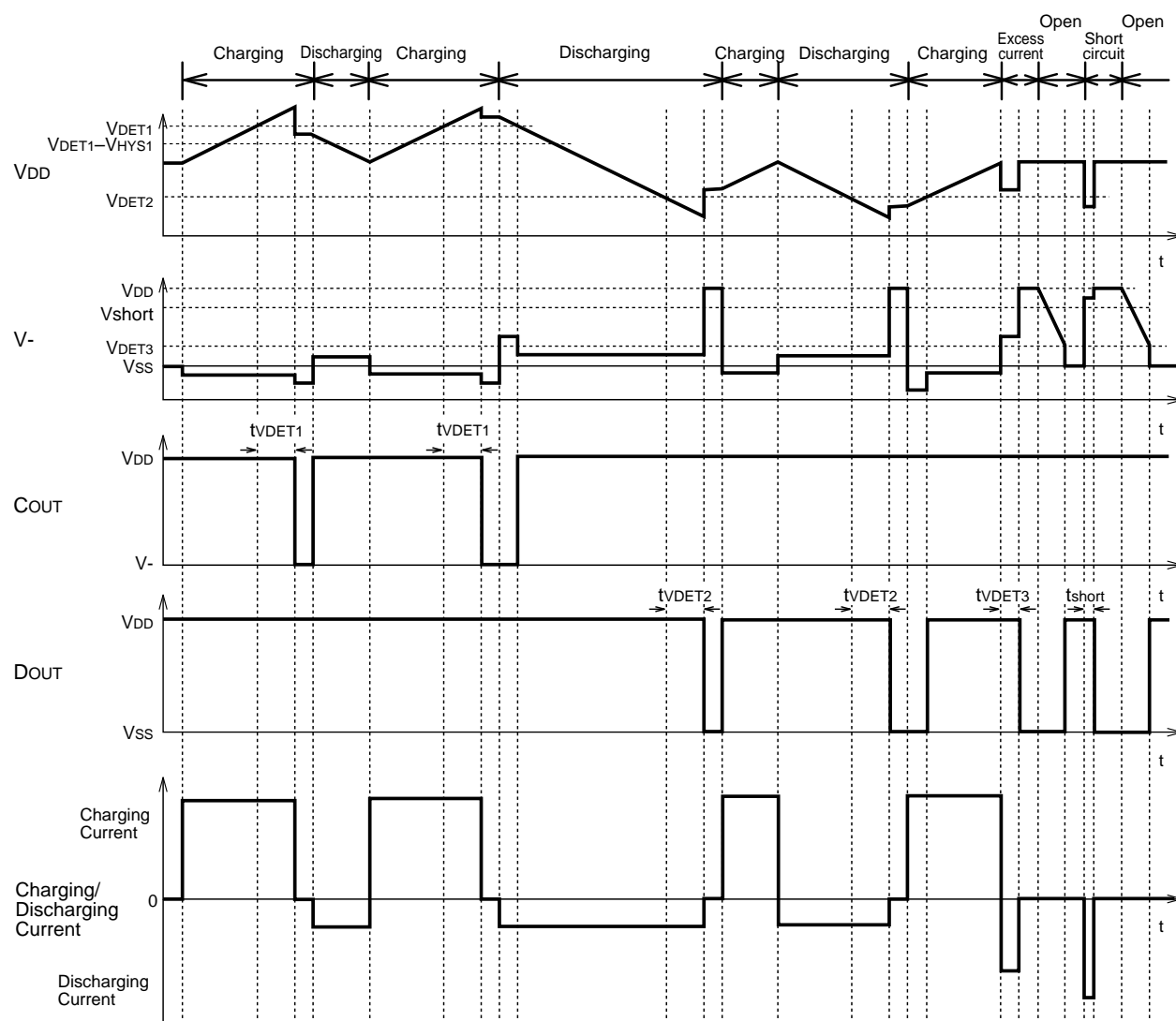
T_{opt}=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD1}	Operating input voltage	Voltage defined as V _{DD} –V _{SS}	1.5		10	V
V _{st}	Minimum operating voltage for 0V charging	Voltage defined as V _{DD} –V _– , V _{DD} –V _{SS} =0V			1.2	V
V _{DET1}	Over-charge threshold voltage	Detect rising edge of supply voltage	4.30	4.35	4.40	V
V _{HYS1}	Over-charge threshold hysteresis range		0.15	0.20	0.25	V
t _{VDET1}	Output delay time of over-charge	C ₃ =0.01μF, V _{DD} =3.6V→4.4V	55	80	105	ms
V _{DET2}	Over-discharge threshold voltage	Detect falling edge of supply voltage	2.437	2.500	2.563	V
t _{VDET2}	Output delay time of over-discharge	V _{DD} =3.6V→2.4V	7	10	13	ms
V _{DET3}	Excess current threshold voltage	Detect rising edge of “V-” pin voltage	0.17	0.20	0.23	V
t _{VDET3}	Output delay time of excess current	V _{DD} =3.0V	9	13	17	ms
V _{short}	Short detection voltage	V _{DD} =3.0V	V _{DD} –1.1	V _{DD} –0.8	V _{DD} –0.5	V
t _{short}	Output delay time of short detection	V _{DD} =3.0V		5	50	μs
R _{short}	Reset resistance for excess current protection	V _{DD} =3.6V, V _– =1.0V	50	100	150	kΩ
V _{OL1}	Nch ON voltage of C _{OUT}	I _{OL} =50μA, V _{DD} =4.4V		0.2	0.5	V
V _{OH1}	Pch ON voltage of C _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.8		V
V _{OL2}	Nch ON voltage of D _{OUT}	I _{OL} =50μA, V _{DD} =2.4V		0.2	0.5	V
V _{OH2}	Pch ON voltage of D _{OUT}	I _{OH} =–50μA, V _{DD} =3.9V	3.4	3.7		V
I _{DD}	Supply current	V _{DD} =3.9V, V _– =0V		3.0	6.0	μA
I _{standby}	Standby current	V _{DD} =2.0V		0.3	0.6	μA

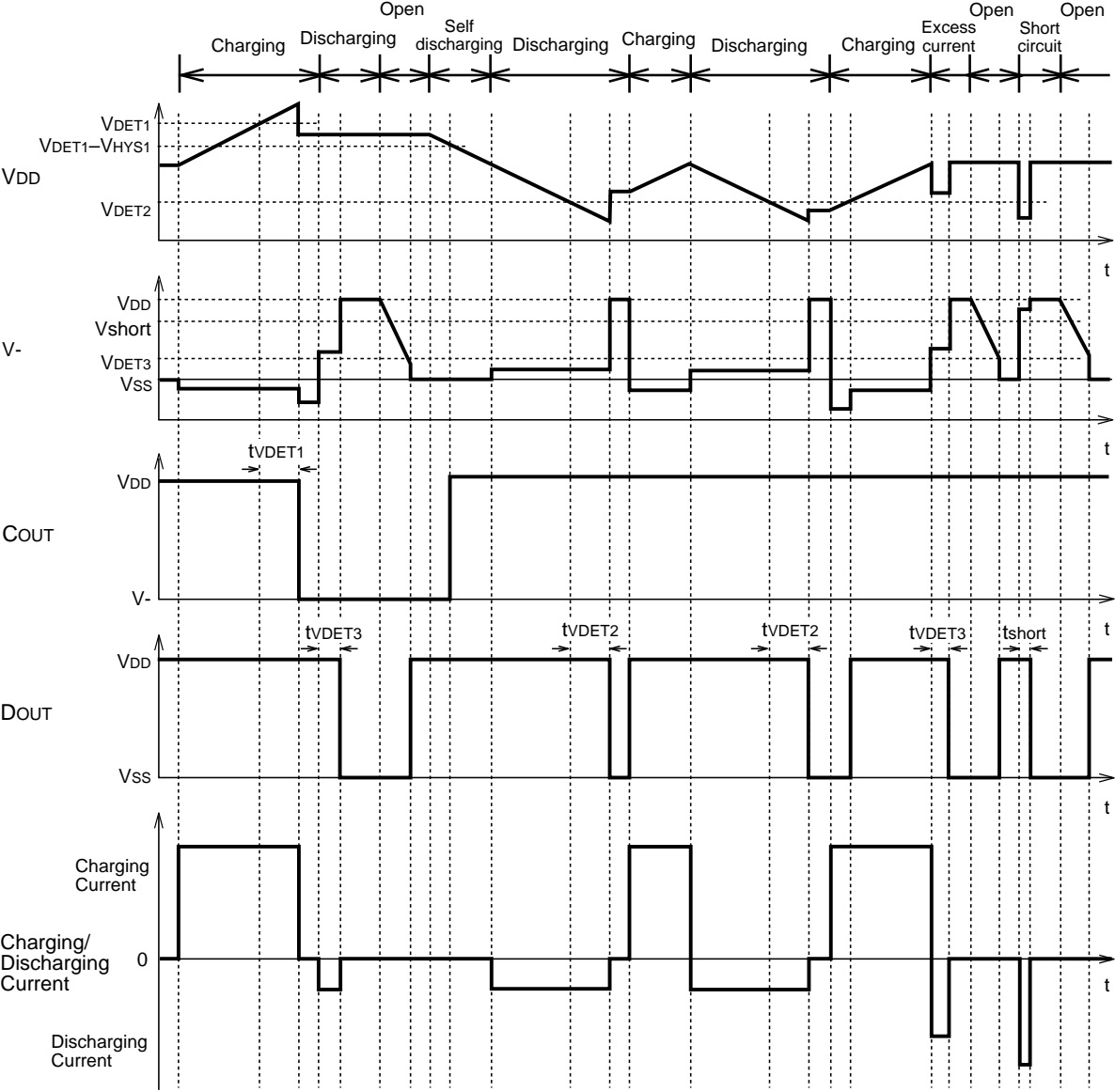
■ *) Please refer to Test Circuit unless otherwise specified.

TIMING DIAGRAM

• RN5VM1××C



• RN5VM1××D



OPERATION

• VD1/Over-Charge Detector

- The VD1 monitors VDD pin voltage. When the VDD voltage crosses over-charge detector threshold VDET1 from a low value to a value higher than the VDET1, the VD1 can sense over-charging and an external charge control Nch-MOS-FET turns to “OFF” with COUT pin being at “L”.
- An output delay time for over-charge detection can be set by an external capacitor C3 connecting the Vss pin and Ct pin. The external capacitor can make a delay time from a moment detecting over-charge to a time output a signal which enables charge control Nch-MOS-FET for turning to “OFF”. Though the VDD voltage would be going up to a higher level than VDET1 if it is within a time period of the output delay time, VD1 would not output a signal for turning “OFF” of charge control Nch-MOS-FET. The output delay time can be calculated as below:

$$t_{VDET1} = \frac{C3 \times (V_{DD} - 0.7)}{0.48 \times 10^{-6}}$$

- A level shifter incorporated in a buffer driver for the COUT pin makes the “L” of COUT pin to the V- pin voltage and the “H” of COUT pin is set to VDD voltage with CMOS buffer.

Reset conditions from overcharging of RN5VM1××C

- There can be two cases to reset the VD1 making the COUT pin level to “H” again after detecting over-charge. Resetting the VD1 makes the charging system ready for resumption of charging process.
The first case is in such condition that a time when the VDD voltage is coming down to a level lower than “VDET1-VHYS1”. While in the second case, disconnecting a charger from the battery pack can make the VD1 resetting when the VDD level is within hysteresis width ($V_{DET1} - V_{HYS1} \leq V_{DD} < V_{DET1}$)
- After detecting over-charge with the VDD voltage of higher than VDET1, connecting system load to the battery pack makes load current allowable through parasitic diode of external charge control Nch-MOS-FET. The COUT level would be “H” when the VDD level is coming down to a level below the VDET1 by continuous drawing of load current.

Reset conditions from overcharging of RN5VM1××D

- After detecting over-charge, the VD1 would not be released and COUT level would not switch to “H” again with the exception that a cell voltage reaches to a lower value than “VDET1-VHYS1” by self discharge of cell or else. After detecting over-charge, when the VDD level stays at a value higher than “VDET1-VHYS1”, to connect battery pack to a system load makes battery pack being disabled at for charging or discharging because of excess current detector operated being DOUT “L”.

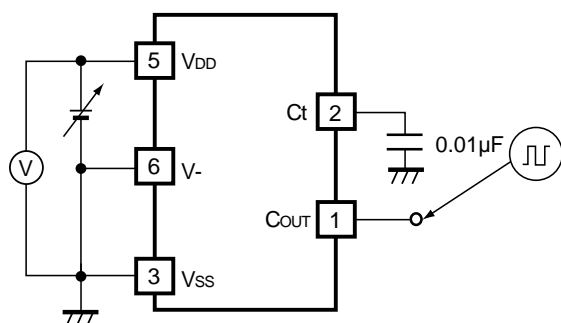
• VD2/Over-Discharge Detector

- The VD2 monitors a VDD pin voltage. When the VDD voltage crosses the over-discharge detector threshold VDET2 from a high value to a value lower than the VDET2, the VD2 can sense an over-discharging and the external discharge control Nch-MOS-FET turns to “OFF” with the DOUT pin being at “L”.
- Resetting the VD2 with the DOUT pin level being “H” again after detecting over-discharge is only possible by connecting a charger to the battery pack. When the VDD voltage stays under over-discharge detector threshold VDET2 charge current can flow through parasitic diode of external discharge control Nch-MOS-FET, then after the VDD voltage comes up to a value larger than VDET2 discharging process would be advanced through “ON” state discharge control Nch-MOS-FET. Connecting a charger to the battery pack makes the DOUT level being “H” instantaneously when the VDD voltage is higher than VDET2.
- When a cell voltage equals to zero, connecting charger to the battery pack makes the system allowable for charge with higher charge voltage than Vst, 1.2V Max.
- An output delay time for the over-discharge detection is fixed internally. Though the VDD voltage would be going down to a lower level than VDET2 if it is within a time period of the output delay time, VD2 would not output a signal for turning “OFF” of discharge control Nch-MOS-FET.
- After detection of an over-discharge by VD2, supply current would be reduced to 0.3μA TYP. at VDD=2.0V and into standby, only the charger detector is operating.
- The output type of DOUT pin is CMOS having “H” level of VDD and “L” level of Vss.

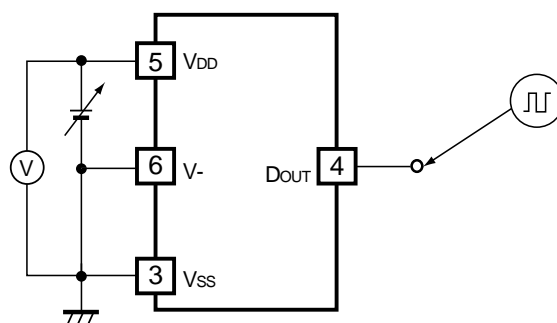
• VD3/Excess Current Detector, Short Circuit Protector

- Both of the excess current detector and short circuit protector can work when both control Nch-MOS-FETs are in “ON” state.
When the V- pin voltage is going up to a value between the short protection voltage Vshort and excess current threshold VDET3, the excess current detector operates and further soaring of V- pin voltage higher than Vshort makes the short circuit protector enabled. As a result the external discharge control Nch-MOS-FET turns to “OFF” with the DOUT pin being at “L”.
- An output delay time for the excess current detector is internally fixed, 13ms TYP. at VDD=3.0V. A quick recovery of V- pin level from a value between Vshort and VDET3 within the delay time keeps the discharge control FET staying “ON” state.
When the short circuit protector is enabled, the DOUT would be “L” and its delay time would be 5μs TYP.
- The V- pin has a built-in pull down resistor, TYP.100kΩ, connected to the Vss pin.
After an excess current or short circuit protection is detected, removing a cause of excess current or external short circuit makes an external discharge control Nch-MOS-FET to an “ON” state automatically with the V- pin level being down to the Vss level through the built-in pull down resistor.
- When VDD voltage is higher than VDET2 at a time when the excess current is detected the 5VM does not enter a standby mode, while VDD voltage is lower than VDET2 the 5VM enters a standby mode.
After detecting short circuit the 5VM will not enter a standby mode.

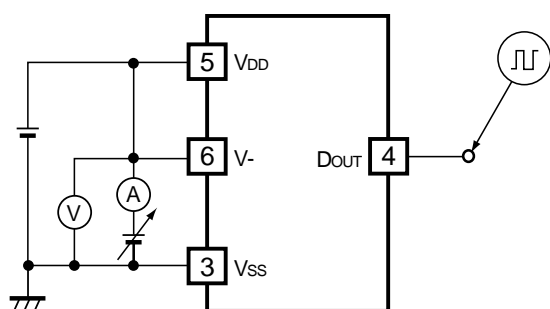
TEST CIRCUIT



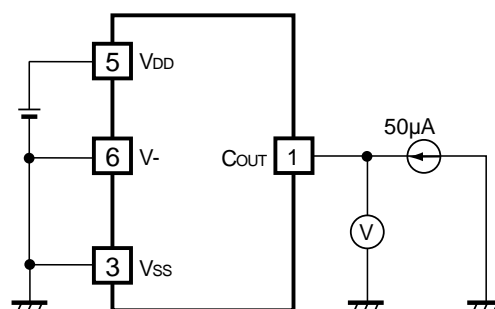
Test Circuit 1



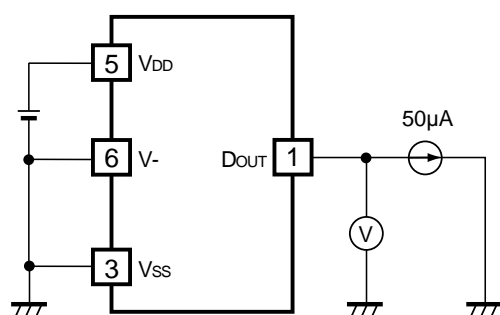
Test Circuit 2



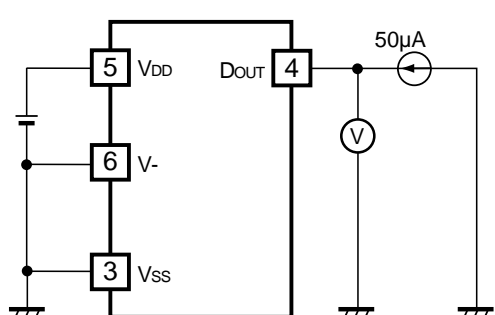
Test Circuit 3



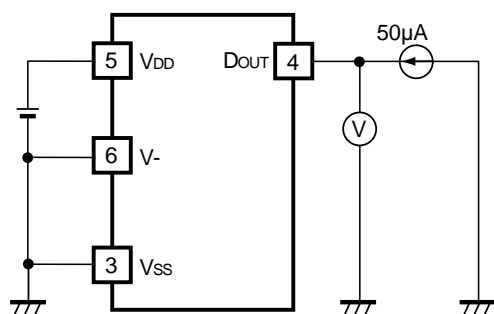
Test Circuit 4



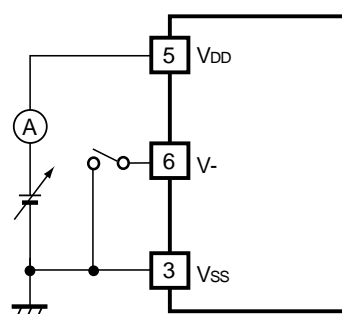
Test Circuit 5



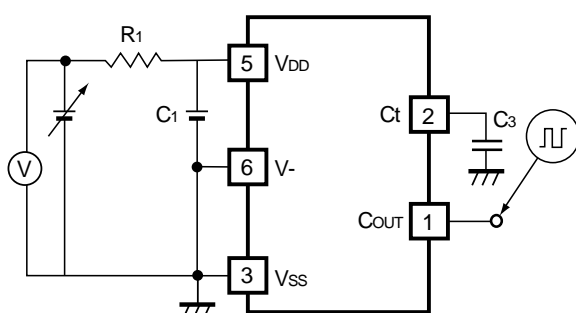
Test Circuit 6



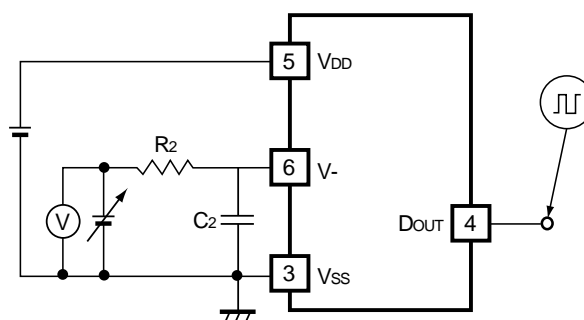
Test Circuit 7



Test Circuit 8



Test Circuit 9



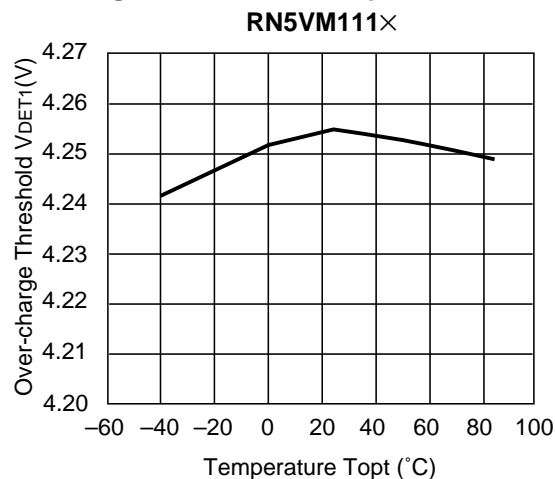
Test Circuit 10

The typical characteristics were obtained by use of these test circuits

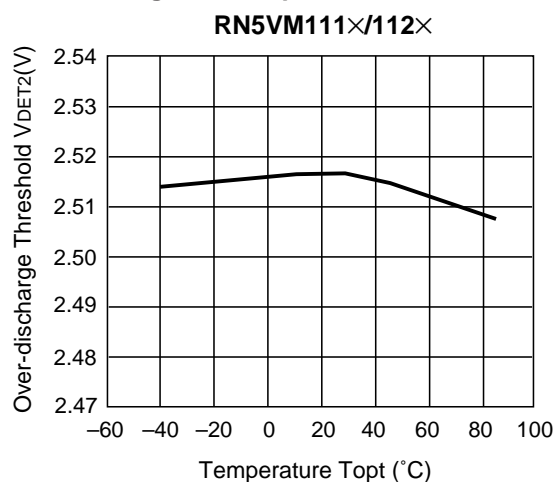
- Test Circuit 1 : Typical characteristics 1) 5) 9) 16)
- Test Circuit 2 : Typical characteristics 2) 6)
- Test Circuit 3 : Typical characteristics 3) 4) 7) 8) 18)
- Test Circuit 4 : Typical characteristics 12)
- Test Circuit 5 : Typical characteristics 13)
- Test Circuit 6 : Typical characteristics 14)
- Test Circuit 7 : Typical characteristics 15)
- Test Circuit 8 : Typical characteristics 10) 11)
- Test Circuit 9 : Typical characteristics 20)
- Test Circuit 10: Typical characteristics 17) 19)

TYPICAL CHARACTERISTICS

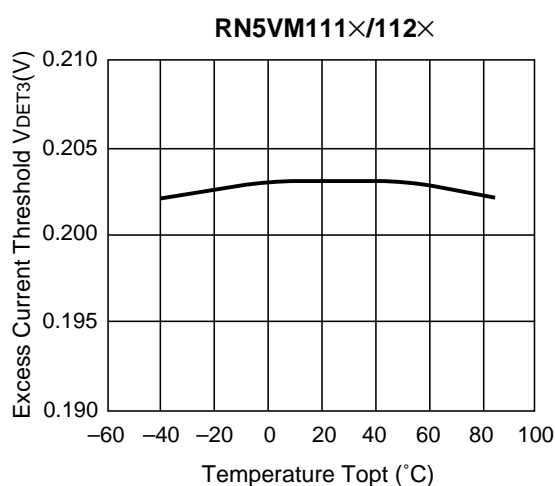
1) Over-charge threshold vs. Temperature



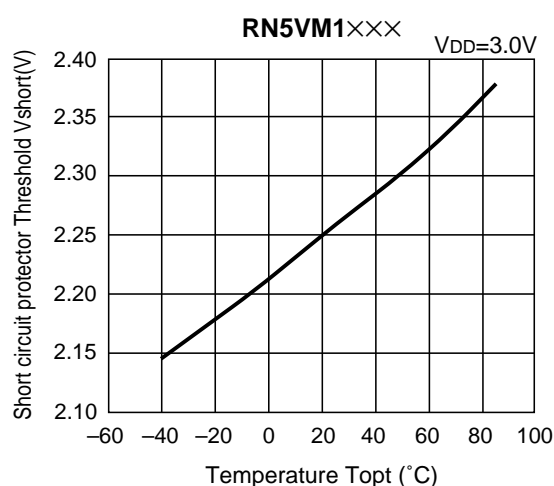
2) Over-discharge vs. Temperature



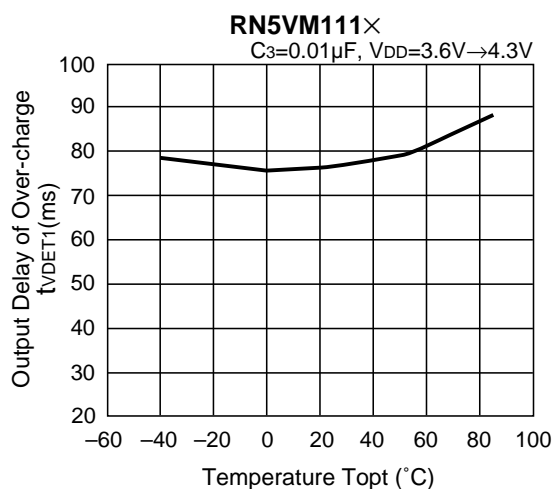
3) Excess Current Threshold vs. Temperature



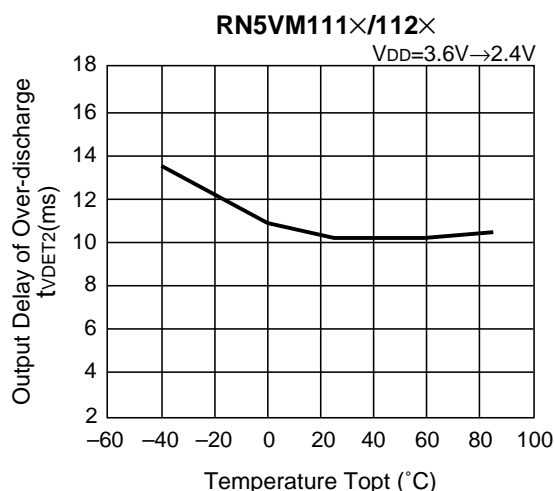
4) Short circuit protector Threshold vs. Temperature



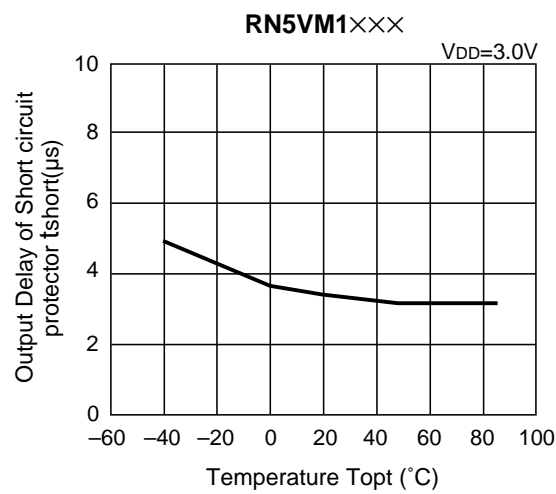
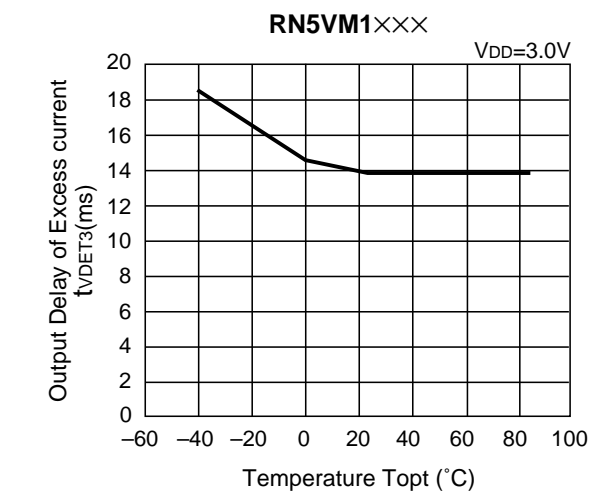
5) Output Delay of Over-charge vs. Temperature



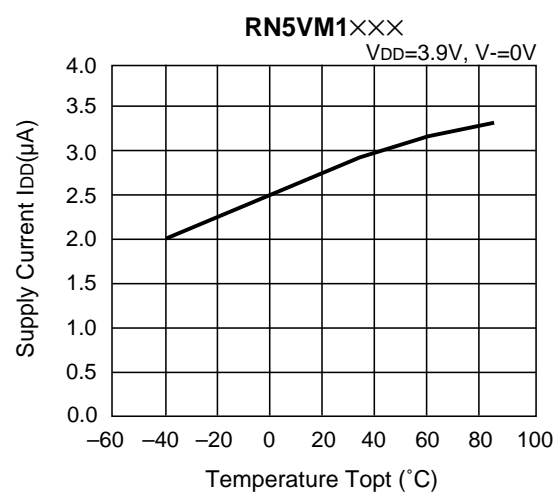
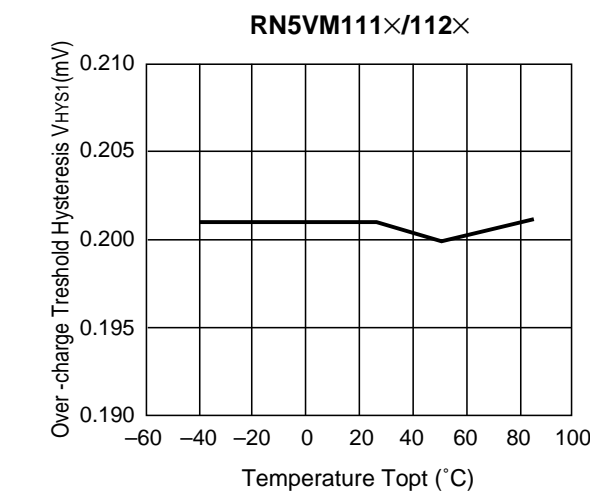
6) Output Delay of Over-discharge vs. Temperature



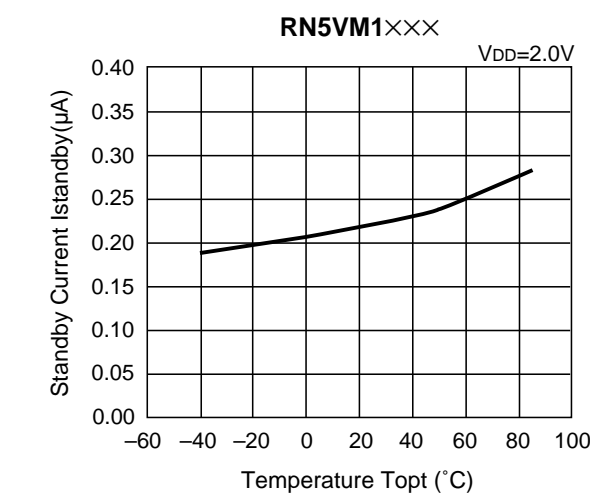
7) Output Delay of Excess current vs. Temperature 8) Output Delay of Short circuit protector vs. Temperature



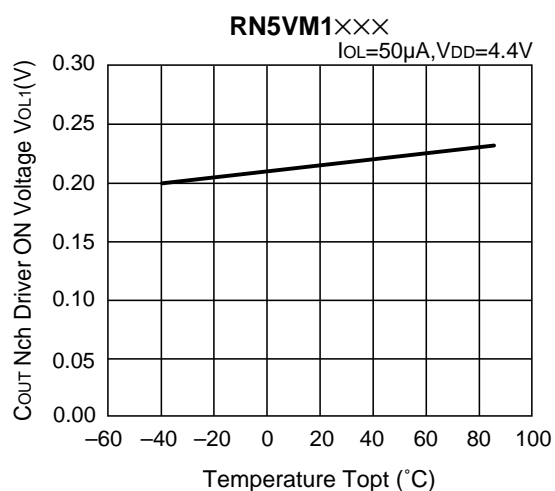
9) Over-charge Threshold Hysteresis vs. Temperature 10) Supply Current vs. Temperature



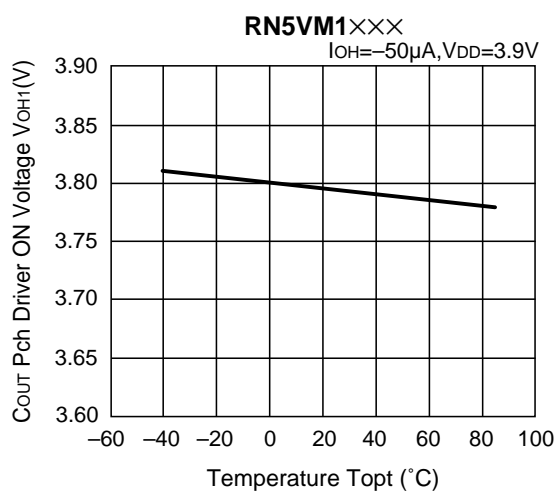
11) Standby Current vs. Temperature



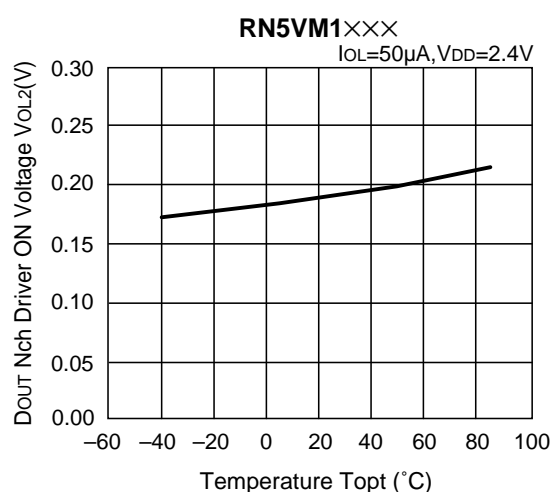
12) Cout Nch Driver ON Voltage vs. Temperature



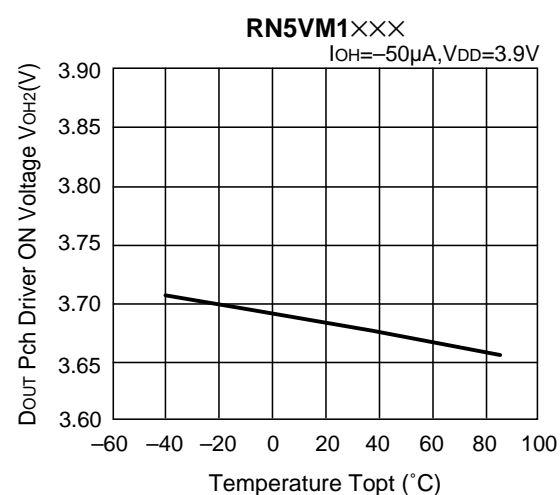
13) Cout Pch Driver ON Voltage vs. Temperature



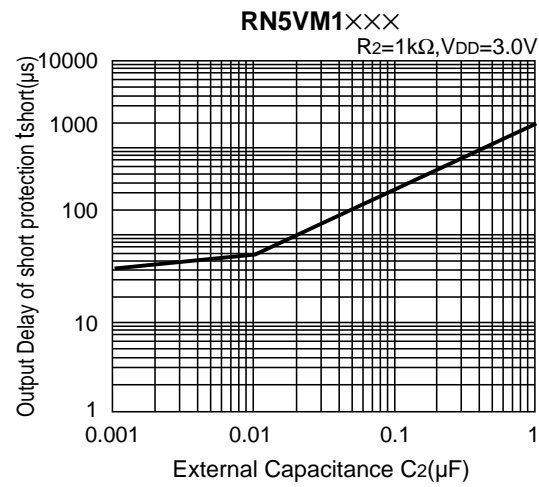
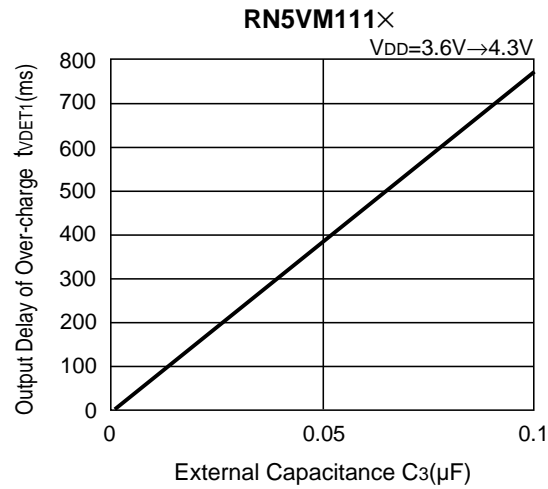
14) Dout Nch Driver ON Voltage vs. Temperature



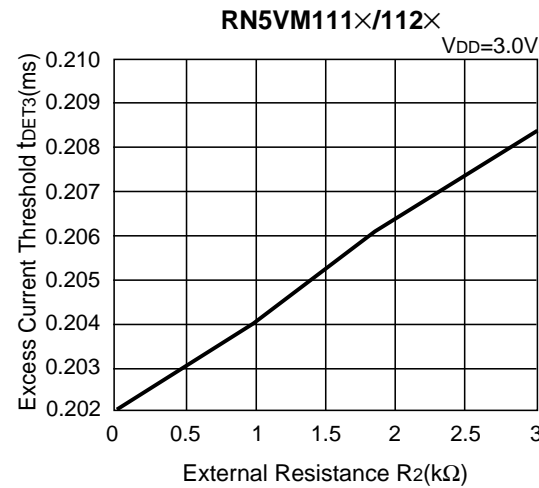
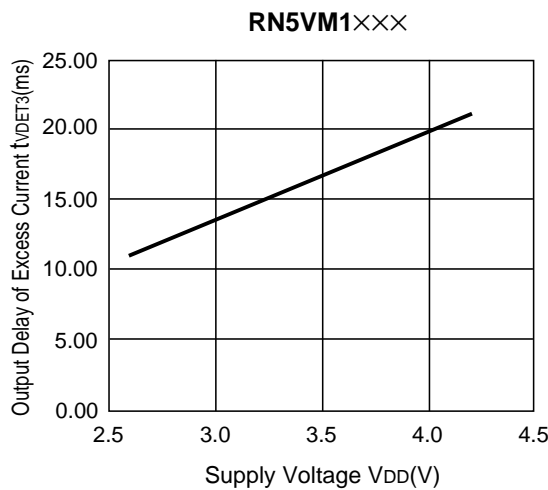
15) Dout Pch Driver ON Voltage vs. Temperature



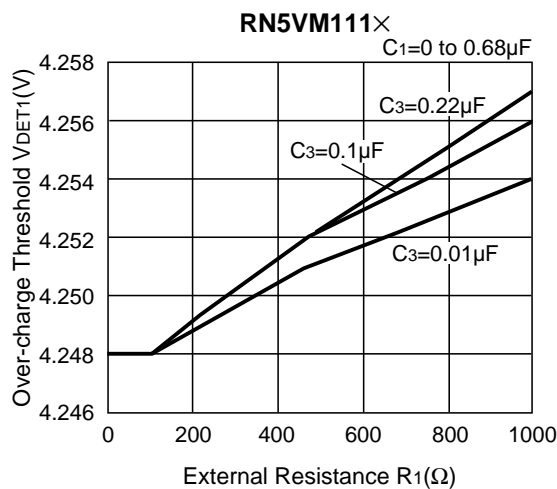
16) Output Delay of Over-charge vs. Capacitance C3 17) Output Delay of Short protection vs. Capacitance C2



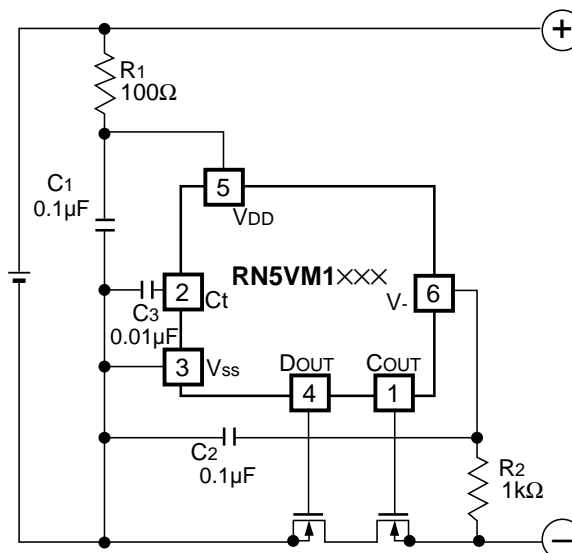
18) Output Delay of Excess Current vs. VDD 19) Excess Current Threshold vs. External resistance R2



20) Over-charge Threshold vs. External Resistance R1



TYPICAL APPLICATION



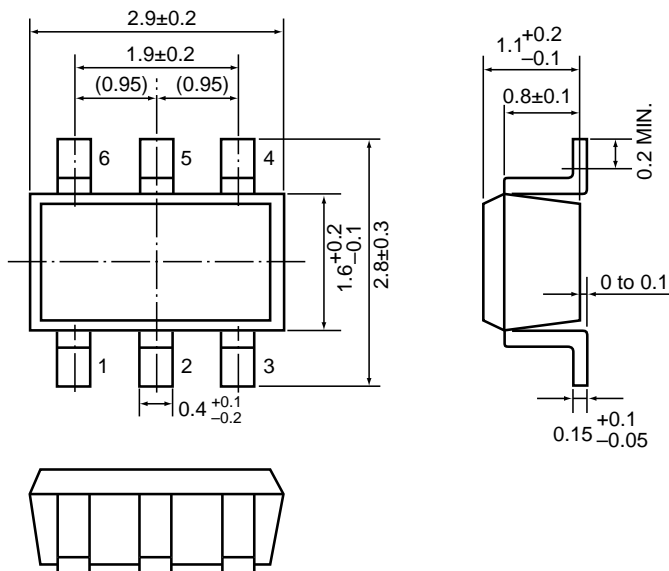
NOTE ON EXTERNAL COMPONENTS

- R_1 and C_1 will stabilize a supply voltage to the RN5VM. A recommended R_1 value is less than $1k\Omega$.
A larger value of R_1 leads higher detection voltage, makes some errors, because of shoot through current flowed in the RN5VM.
- R_2 and C_2 will stabilize a V- pin voltage. The resetting from over-discharge with connecting charger possibly be disabled by larger value of R_2 . Recommended value is less than $1k\Omega$.
After an over-charge detection, a system may not draw load current when a battery pack is connected to it in the C version with R_2 and C_2 time constants at relatively larger settings.
Recommended C_2 value is less than $1\mu F$.
- R_1 and R_2 can operate as a current limiter against setting cell reverse direction or for applying excess charging voltage to the 5VM. While smaller R_1 and R_2 may cause an over power dissipation rating of the RN5VM and a total of " R_1+R_2 " should be more than $1k\Omega$.
- The time constants $R_1 \times C_1$ or $R_2 \times C_2$ must have a relations as below:

$$R_1 \times C_1 \leq R_2 \times C_2$$
 Because in case that $R_1 \times C_1$, time constant for V_{DD} pin, would be larger than $R_2 \times C_2$, time constant for V- pin, then the RN5VM might be into a standby mode after detecting excess current or short circuit current.

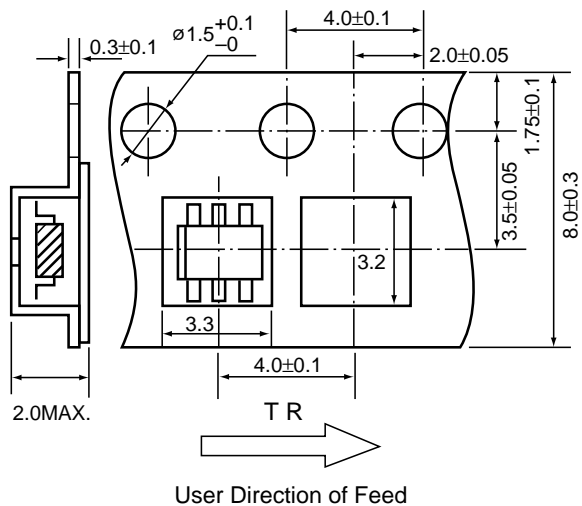
PACKAGE DIMENSION (Unit : mm)

• SOT-23-6



TAPING SPECIFICATION (Unit : mm)

• SOT-23-6





RICOH COMPANY, LTD.
ELECTRONIC DEVICES DIVISION

HEADQUARTERS

13-1, Himemuro-cho, Ikeda City, Osaka 563-8501, JAPAN
Phone 81-727-53-1111 Fax 81-727-53-6011

YOKOHAMA OFFICE (International Sales)

3-2-3, Shin-Yokohama, Kohoku-ku, Yokohama City, Kanagawa 222-8530,
JAPAN
Phone 81-45-477-1697 Fax 81-45-477-1694 • 1695
<http://www.ricoh.co.jp/LSI/english/>

RICOH CORPORATION
ELECTRONIC DEVICES DIVISION

SAN JOSE OFFICE

3001 Orchard Parkway, San Jose, CA 95134-2088, U.S.A.
Phone 1-408-432-8800 Fax 1-408-432-8375